CMOS Look-Ahead Carry Generator

High-Voltage Types (20-Volt Rating)

The RCA-CD40182B is a high-speed look-ahead carry generator capable of anticipating a carry across four binary adders or groups of adders. The CD40182B is cascadable to perform full look-ahead across n-bit adders. Carry, propagate-carry, and generate-carry functions are provided as enumerated in the terminal designation below.

The CD40182B, when used in conjunction with the CD40181B arithmetic logic unit (ALU), provides full high-speed look-ahead carry capability for up to n-bit words. Each CD40182B generates the look-ahead (anticipated carry) across a group of four ALU's. In addition, other CD40182B's may be employed to anticipate the carry across sections of four look-ahead blocks up to n-bits. Carry inputs and outputs of the CD40181B are active-high logic, and carry-generate (G) and carry-propagate (P) outputs are active-low. Therefore the inputs and outputs of the CD40182B are compatible.

The CD40182B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).

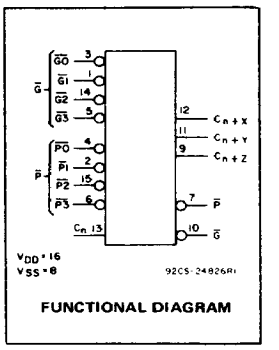
The CD40182B is similar to industry type MC14582.

Features:

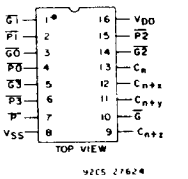
- Generates high-speed carry across four adders or adder groups
- High-speed operations:
  $t_{PHL} = t_{PLH}$ = 100 ns (typ.) @ V_{DD} = 10 V
- Cascadable for fast carries over N bits
- Designed for use with CD40181B ALU
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) = 1 V at V_{DD} = 5 V, 2 V at V_{DD} = 10 V, 2.5 V at V_{DD} = 15 V
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- High-speed parallel arithmetic units
- Multi-level look-ahead carry generation for long word lengths



FUNCTIONAL DIAGRAM



TERMINAL ASSIGNMENT

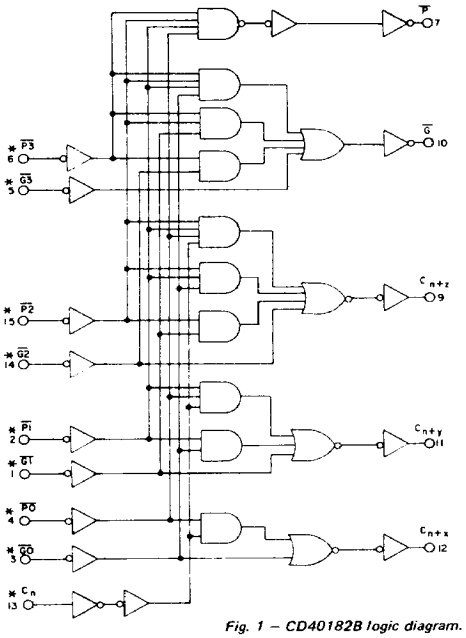
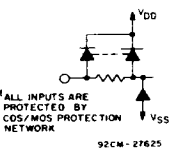


Fig. 1 – CD40182B logic diagram.



TERMINAL DESIGNATIONS

DESIGNATION	TERM.	FUNCTION
$\overline{G0}, \overline{G1}, \overline{G2}, \overline{G3}$	3, 1, 14, 5	Active-Low Carry-Generate Inputs
$\overline{P0}, \overline{P1}, \overline{P2}, \overline{P3}$	4, 2, 15, 6	Active-Low Carry-Propagate Inputs
C_n	13	Active-High Carry Input
$C_{n+x}, C_{n+y}, C_{n+z}$	12, 11, 9	Active-High Carry Outputs
$\overline{G}$	10	Active-Low Group Carry-Generate Output
$\overline{P}$	7	Active-Low Group Carry-Propagate Output

CD40182B Logic Equations:

$$C_{n+x} = G0 + P0 \cdot C_n$$

$$C_{n+y} = G1 + P1 \cdot G0 + P1 \cdot P0 \cdot C_n$$

$$C_{n+z} = G2 + P2 \cdot G1 + P2 \cdot P1 \cdot G0 + P2 \cdot P1 \cdot P0 \cdot C_n$$

$$\overline{G} = \overline{G3 + P3 \cdot G2 + P3 \cdot P2 \cdot G1 + P3 \cdot P2 \cdot P1 \cdot G0}$$

$$\overline{P} = \overline{P3 \cdot P2 \cdot P1 \cdot P0}$$

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -40 to +60°C (PACKAGE TYPE E) ..... 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) ..... Derate Linearly at 12 mW/°C to 200 mW
For T_A = -55 to +100°C (PACKAGE TYPES D, F, K) ..... 500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K) ..... Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR:
For T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, K, H ..... -55 to +125°C
PACKAGE TYPE E ..... -40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. ..... +265°C

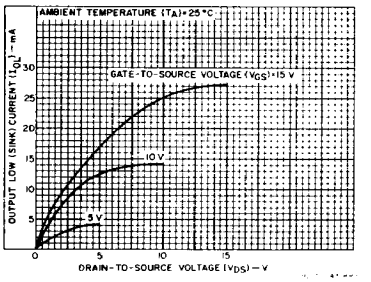


Fig. 2 — Typical output low (sink) current characteristics.

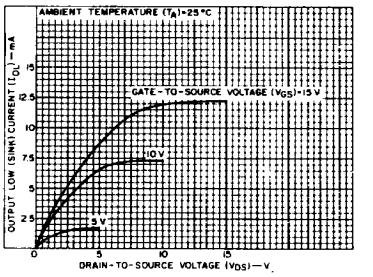


Fig. 3 — Minimum output low (sink) current characteristics.

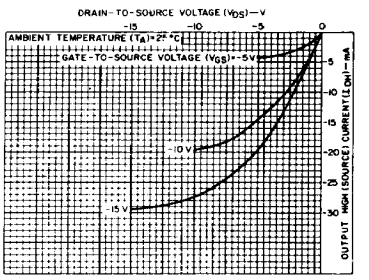


Fig. 4 — Typical output high (source) current characteristics.

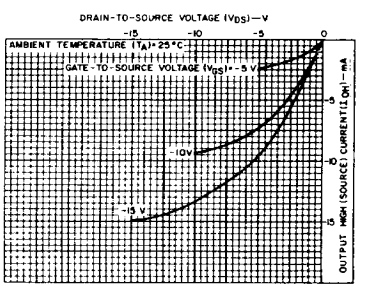


Fig. 5 — Minimum output high (source) current characteristics.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at -55 +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Package							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	5	5	150	150	–	0.04	5	µA
	–	0,10	10	10	10	300	300	–	0.04	10	
	–	0,15	15	20	20	600	600	–	0.04	20	
	–	0,20	20	100	100	3000	3000	–	0.08	100	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	–	
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	–	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	–	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5, 4.5	–	5	1.5				—	—	1.5	V
	1, 9	–	10	3				—	—	3	
	1.5,13.5	–	15	4				—	—	4	
Input High Voltage, V_{IH} Min.	0.5, 4.5	–	5	3.5				3.5	—	—	
	1, 9	–	10	7				7	—	—	
	1.5,13.5	–	15	11				11	—	—	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$±10^{-5}$	±0.1	µA

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Typ.	Max.	
Propagation Delay Time: t_{PHL}, t_{PLH} P, G In to P, G Out and Carry Outs	5	200	400	ns
	10	100	200	
	15	75	150	
C_n to Carry Outs	5	240	480	ns
	10	120	240	
	15	90	180	
Transition Time: t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Input Capacitance C_{IN} (Any Input)	—	5	7.5	pF

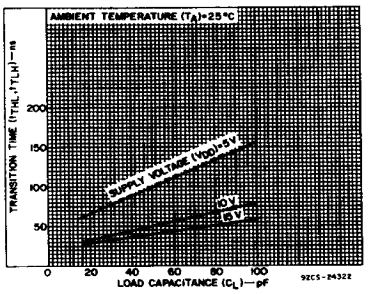


Fig. 6 – Typical transition time as a function of load capacitance.

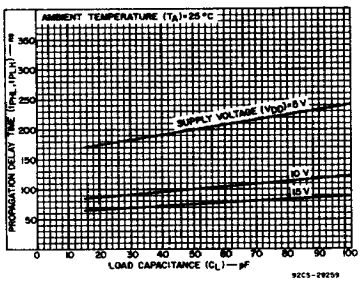


Fig. 7 – Typical propagation delay time as a function of load capacitance (P, G In to P, G Out and Carry-Outs).

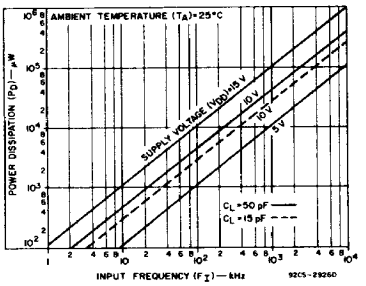


Fig. 8 – Typical power dissipation as a function of input frequency.

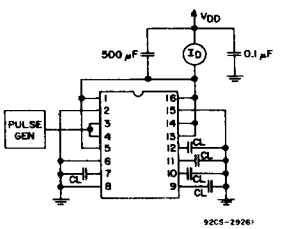


Fig. 9 – Power dissipation test circuit.

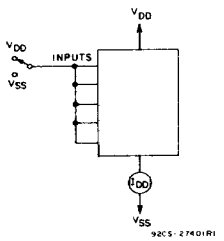


Fig. 10 – Quiescent device current test circuit.

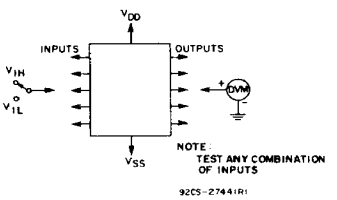


Fig. 11 – Input voltage test circuit.

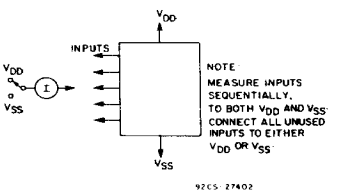


Fig. 12 – Input current test circuit.

Applications

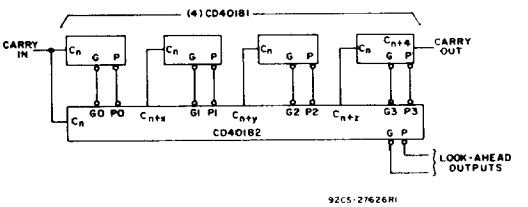


Fig. 13 – 16-Bit two-level look-ahead ALU.

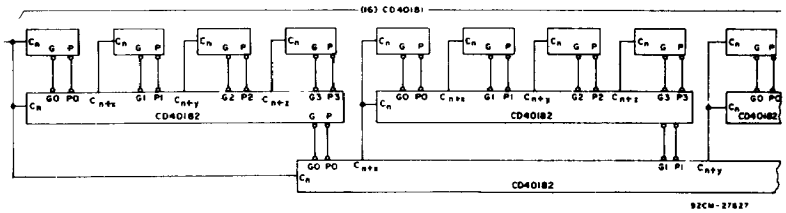


Fig. 14 – 64-Bit full carry look-ahead ALU in 3 levels.

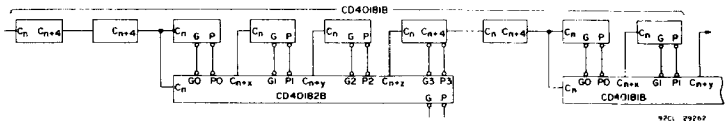
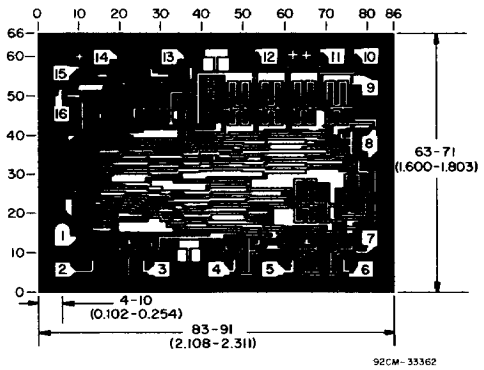


Fig. 15 – Combined two-level look-ahead and ripple-carry ALU.

DIMENSIONS AND PAD LAYOUT FOR CD40182BH



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.